

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	103	(gate near6 surround\$3 near6 source near6 drain) and (locos fox sti (isolation near1 trench)) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 13:57
L4	2	("6121657").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:21
L5	0	4 and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 13:57
L6	989364	4 and gate (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:22
L7	1	4 and gate and (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:22
L8	29	(US-20020084485-\$ or US-20020145164-\$ or US-20030001196-\$ or US-20030006463-\$ or US-20030107103-\$ or US-20040113207-\$ or US-20040164354-\$ or US-20040195621-\$ or US-20020086461-\$).did. or (US-5072266-\$ or US-5159431-\$ or US-5241205-\$ or US-5451799-\$ or US-5936265-\$ or US-6091630-\$ or US-6191450-\$ or US-6310380-\$ or US-6504213-\$ or US-6576959-\$ or US-6586807-\$ or US-6611027-\$ or US-6642540-\$ or US-6737688-\$ or US-6764892-\$ or US-6787410-\$ or US-6867476-\$ or US-6897499-\$ or US-6121657-\$).did. or (US-20010011753-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/12/27 15:45
L9	0	8 and gidi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:03

L10	0	8 and gate-induced adj drain adj leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:03
L11	6	(source drain) near6 (separat\$3 distance spaced adj apart) near6 (sti locos fox) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:06
L12	0	(source drain) near6 (separat\$3 distance spaced adj apart) near6 (sti locos fox) and cmos near6 (imaging imager)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:07
L13	201	(source drain) near9 (separat\$3 distance spaced adj apart) near9 (sti locos fox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:07
L14	6	(source drain) near9 (separat\$3 distance spaced adj apart) near9 (sti locos fox) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:39
L15	126	(source drain) near9 (separat\$3 distance spaced adj apart) near9 (sti locos fox) and (mos mosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:08
L16	53	(source drain) near9 (separat\$3 distance spaced adj apart) near9 (sti locos fox) and (mos mosfet cmos cmosfet).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:29
L17	0	diffusion adj length and mos adj transistor and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:29
L18	4669	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:45
L19	0	18:and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab,clm. and gate near6 (surround\$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48

L20	0	18 and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab,clm. and gate near6 (surround\$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48
L21	0	18 and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab,clm. and gate near6 (surround\$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square) and (gate adj induced adj drain adj leak\$3 gidl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48
S1	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 12:51
S2	2	(("6504213") or ("6611027")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/09 20:30
S3	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 15:58
S4	267	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06
S5	33	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3) and trap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 20:43
S6	13	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3) and plan adj view and gate near6 length	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 20:51
S7	3027	leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06
S8	247	trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07

S9	234	(trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat\$3)) not S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07
S10	7	(US-20040195621-\$ or US-20030107103-\$ or US-20030001196-\$).did. or (US-6611027-\$ or US-6504213-\$ or US-6787410-\$ or US-6091630-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 21:39
S11	0	(2003/0006463).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:39
S12	2	("20030006463").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:41
S13	2	jp-2001204272\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:10
S14	24	drain adj2 region near10 (separated apart spaced-apart) near10 (isolation adj structure sti shallow adj trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:11
S15	8	(US-20040195621-\$ or US-20030107103-\$ or US-20030001196-\$ or US-20030006463-\$).did. or (US-6611027-\$ or US-6504213-\$ or US-6787410-\$ or US-6091630-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 23:52
S16	2991	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/01/09 23:52
S17	9	S16 and drain near6 (separated separating separate spaced apart) near6 (sti shallow adj trench adj isolation trench adj isolation trench) and (leakage leaking leak)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/10 00:21
S18	6	"410153".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/10 00:21

S19	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 15:56
S20	2	("20010001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 16:00
S21	2	("20030001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 16:13
S22	3	("6611027").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 17:06
S23	4547	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 17:06
S24	4	S23 and rectangular near4 active adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:06
S25	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 15:50
S26	2	("20010001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 15:50
S27	0	("647604.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:56
S28	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:57

S29	5	("20010001196" or ("6611027")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:59
S30	5	("20030001196" or ("6611027")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:15
S31	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:17
S32	2	("5451799").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:26
S33	6323	(aperture opening) near3 gate and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:28
S34	1045	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:28
S35	168	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti,ab,clm. and (sti locos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:29
S36	44	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti,ab,clm. and (sti locos) and plan adj. view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 11:38
S37	2	("6586807").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:51
S38	0	S37 and (opening aperture) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:43

S39	0	S37 and (opening aperture) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:43
S40	1	S37 and gate adj (insulation oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:52
S41	629	"44" and gate adj (insulation oxide) and misfit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:52
S42	2	S36 and gate adj (insulation oxide) and misfit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 18:14
S43	2	S36 and gate adj (insulation oxide) and misfit and (sti locos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 18:14
S44	66	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab, clm. and (sti locos shallow adj trench adj isolation fox field adj oxide) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:01
S45	1	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab, clm. and (sti locos shallow adj trench adj isolation fox field adj oxide) and plan adj view and (spaced adj apart separation separated) near5 drain near5 (locos sti fox field adj oxide isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:18
S46	5	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab, clm. and (spaced adj apart separation separated) near8 drain near8 (locos sti fox field adj oxide isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20

S47	1	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab, clm. and (spaced adj apart separation separated distance\$1) near8 drain near8 (locos sti fox field adj oxide isolation) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20
S48	1	(aperture opening) near3 gate.ti, ab,clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab, clm. and (spaced adj apart separation separated distance\$1) near8 drain near8 (locos sti fox field adj oxide isolation) and plan adj view and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20